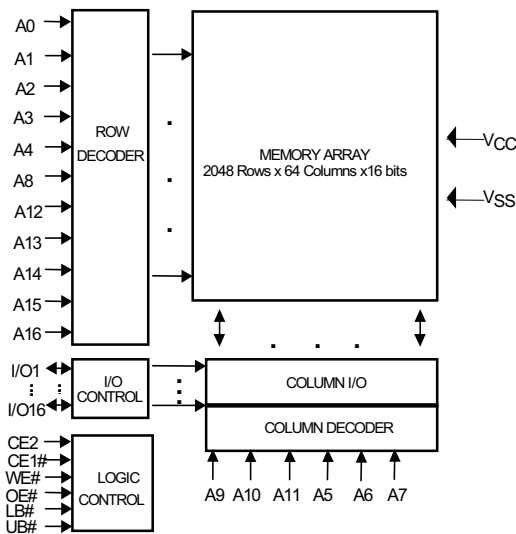




FEATURES

- High speed access time : 70,100 ns (max.)
- Low power consumption :
- Operating : 5 mA (I_{cc1,max.})
Standby : 80uA (max) L-version
25uA (max) LL-version
- Single 2.7-3.3 V_{CC} power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Three- state outputs
- Data Retention Voltage: 1.5 V (min)
- Data byte controll: LB#(I/O1-I/O8)
UB#(I/O9-I/O16)
- Package :
48-pin Ball Tiny BGA (6mmx8mm)
- Product Family : UT62L12916
UT62L12916I

FUNCTIONAL BLOCK DIAGRAM



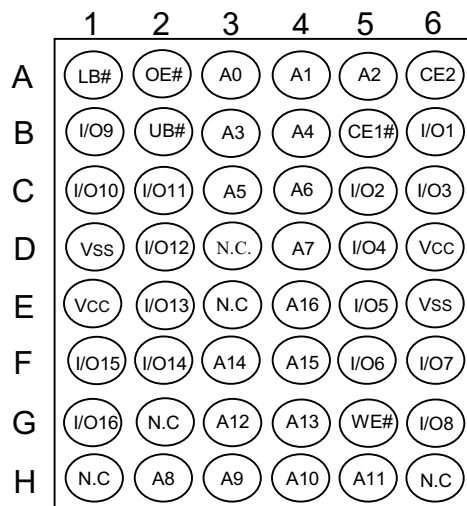
GENERAL DESCRIPTION

The UT62L12916(I) is a 2,097,152-bit low power CMOS static random access memory organized as 131,072 words by 16 bits.

The UT62L12916(I) is designed for low power application. It is particularly well suited for high density low power system application.

The UT62L12916(I) operates from a single 2.7V-3.3V power supply and all inputs and outputs are fully TTL compatible.

PIN CONFIGURATION



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A17	Address Inputs
I/O1 - I/O16	Data Inputs/Outputs
CE1#,CE2	Chip Select Inputs
WE#	Write Enable Input
OE#	Output Enable Input
LB#	Lower-byte Control(I/O1~I/O8)
UB#	Upper-byte Control(I/O9~I/O16)
V _{CC}	Power Supply
V _{SS}	Ground
N.C	No Connection

**ABSOLUTE MAXIMUM RATINGS***

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V _{SS}	V _{TERM}	-0.3 to +4.6	V
Operating Temperature	TA	UT62L12916	0 to +70
		UT62L12916(I)	-40 to +85
Storage Temperature	T _{STG}	-65 to +150	°C
Power Dissipation	P _D	1.0~1.5	W
DC Output Current	I _{OUT}	20	mA
Soldering Temperature	T _{SOLDER}	260 • 10	°C • sec

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE2	CE1#	OE#	WE#	LB#	UB#	I/O1~I/O8	I/O9~I/O16	SUPPLY CURRENT
Not Selected	L	X	X	X	X	X	Hight-Z	Hight-Z	I _{SB} , I _{SB1}
	X	H	X	X	X	X	Hight-Z	Hight-Z	I _{SB} , I _{SB1}
	X	X	X	X	H	H	Hight-Z	Hight-Z	I _{SB} , I _{SB1}
Output Disable	H	L	H	H	X	X	Hight-Z	Hight-Z	I _{CC1} , I _{CC2}
	H	L	H	H	X	L	Hight-Z	Hight-Z	I _{CC1} , I _{CC2}
Read	H	L	L	H	L	H	Dout	Hight-Z	I _{CC1} , I _{CC2}
	H	L	L	H	H	L	Hight-Z	Dout	
	H	L	L	H	L	L	Dout	Dout	
Write	H	L	X	L	L	H	Din	Hight-Z	I _{CC1} , I _{CC2}
	H	L	X	L	H	L	Hight-Z	Din	
	H	L	X	L	L	L	Din	Din	

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 2.7V-3.3V, TA = 0°C to 70°C/-40°C to 85°C (I))

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Power Voltage	V _{CC}		2.7	3.0	3.3	V
Input High Voltage	V _{IH}		2.2	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL}		-0.2	-	0.6	V
Input Leakage Current	I _{LI}	V _{SS} ≤ V _{IN} ≤ V _{CC}		-	1	μA
Output Leakage Current	I _{LO}	V _{SS} ≤ V _{I/O} ≤ V _{CC} CE1# = V _{IH} (min), CE2 = V _{IL} (min) or OE#(min) = V _{IH} or WE # = V _{IL} (max)	-1	-	1	μA
Output High Voltage	V _{OH}	I _{OH} = -1.0mA	2.2	-	-	V
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA	-	-	0.4	V
Operating Power Supply Current	I _{CC}	CE2 = V _{IH} , CE1# = V _{IL} , V _{IN} = V _{IH} or V _{IL} , I _{I/O} = 0mA	-	-	3	mA
Average Operating Current	I _{CC1}	Cycle time = 1μs, 100% duty, I _{I/O} = 0mA CE1# ≤ 0.2V, CE2 ≥ V _{CC} - 0.2V V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V	-	-	5	mA
	I _{CC2}	Cycle time = min, 100% duty, I _{I/O} = 0mA CE1# = V _{IL} , CE2 = V _{IH} , V _{IN} = V _{IH} OR V _{IL}	-	-	35	mA
Standby Power	I _{SB}	CE1# = V _{IH} (min) or CE2 = V _{IH}	-	-	0.5	mA
Supply Current	I _{SB1}	CE1# ≥ V _{CC} - 0.2V or CE2 ≤ 0.2V			80	μA
			L-Version	-	-	25
			LL-Version	-	-	

**CAPACITANCE** ($T_A=25^{\circ}\text{C}$, $f=1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L=30\text{pF}+ 1\text{TTL Load}$

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.7\text{V}-3.3\text{V}$, $T_A = 0^{\circ}\text{C}$ to $70^{\circ}\text{C}/-40^{\circ}\text{C}$ to 85°C (I))**(1) READ CYCLE**

PARAMETER	SYMBOL	UT62L12916(I)-70		UT62L12916(I)-100		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	70	-	100	-	ns
Address Access Time	t_{AA}	-	70	-	100	ns
Chip Enable Access Time	t_{ACE}	-	70	-	100	ns
Output Enable Access Time	t_{OE}	-	35	-	50	ns
UB#,LB# Access Time	t_{BA}	-	70	-	100	ns
Chip Enable to Output in Low-Z	t_{CLZ}^*	10	-	10	-	ns
Output Enable to Output in Low-Z	t_{OLZ}^*	5	-	5	-	ns
UB#,LB# Enable to Output in Low-z	t_{BLZ}	5	-	5	-	ns
Chip Disable to Output in High-Z	t_{CHZ}^*	-	25	-	30	ns
Output Disable to Output in High-Z	t_{OHZ}^*	-	25	-	30	ns
UB#,LB# Disable to Output in High-Z	t_{BHZ}	-	25	-	30	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	ns

(2) WRITE CYCLE

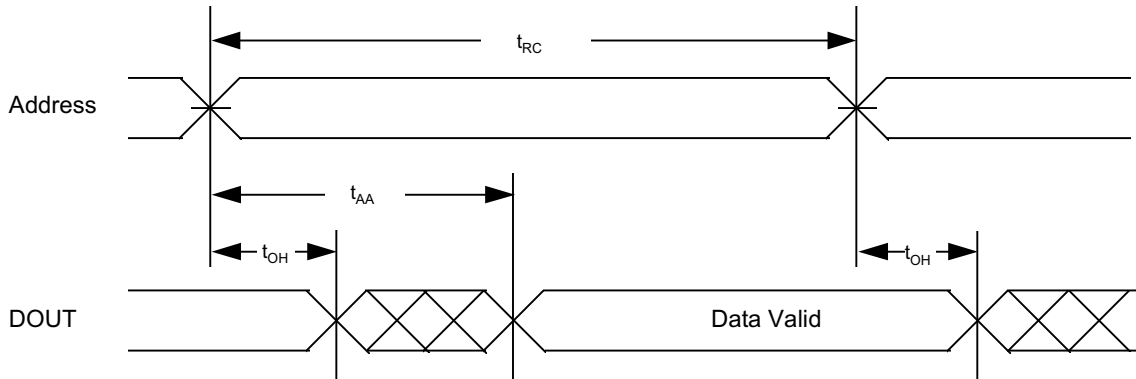
PARAMETER	SYMBOL	UT62L12916(I)-70		UT62L12916(I)-100		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	70	-	100	-	ns
Address Valid to End of Write	t_{AW}	60	-	80	-	ns
Chip Enable to End of Write	t_{CW}	60	-	80	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	ns
UB#,LB# Enable to End of Write	t_{BW}	60	-	80	-	ns
Write Pulse Width	t_{WP}	55	-	70	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	30	-	40	-	ns
Data Hold from End of Write-Time	t_{DH}	0	-	0	-	ns
Output Active from End of Write	t_{OW}^*	60	-	80	-	ns
Write to Output in High-Z	t_{WHZ}^*	0	15	0	15	ns

*These parameters are guaranteed by device characterization, but not production tested.

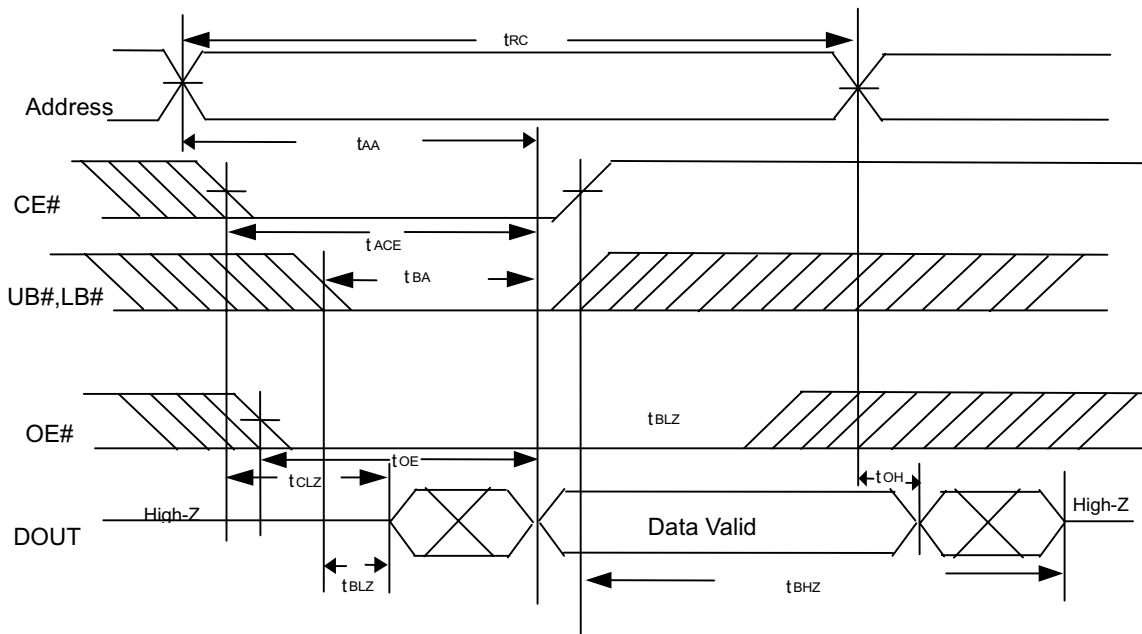


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2,4)



READ CYCLE 2 (CE#, OE# Controlled) (1,3,5,6)

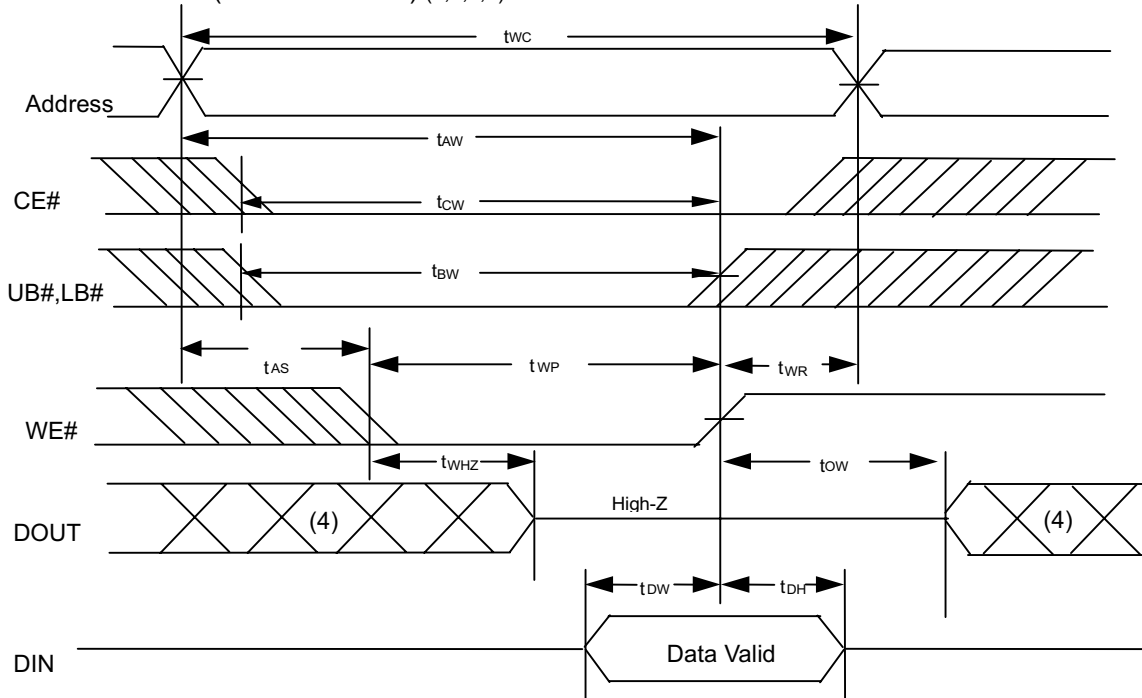


Notes :

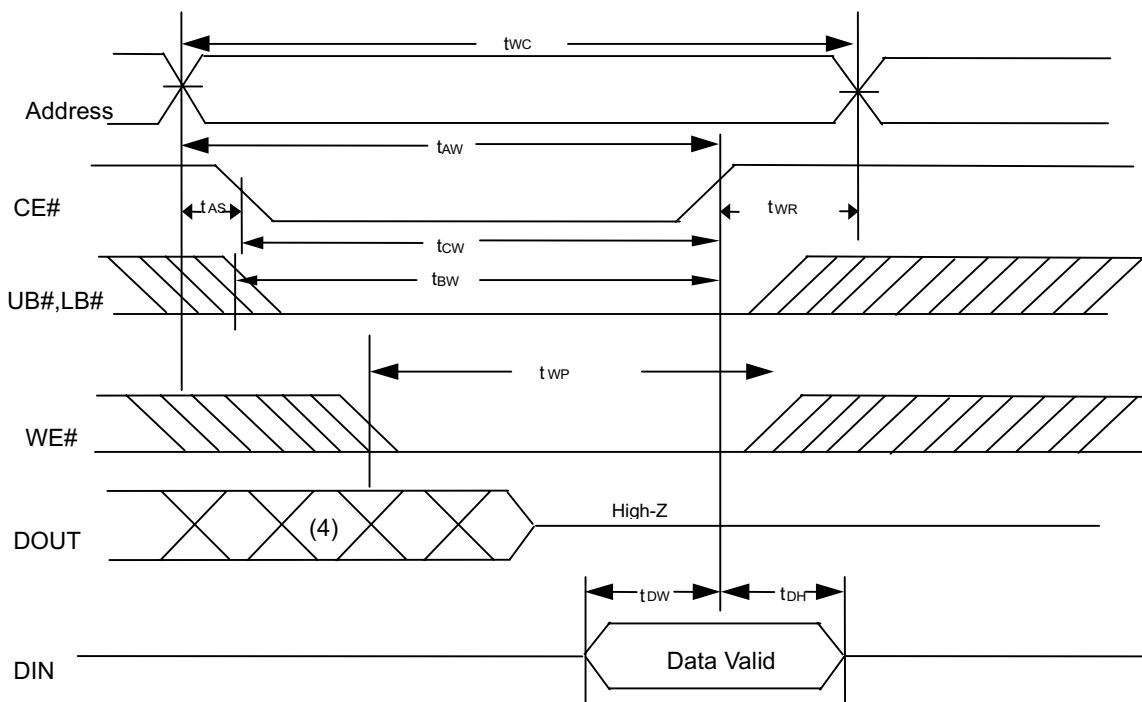
1. WE# is HIGH for read cycle.
2. Device is continuously selected CE#=VIL and UB#=VIH and ,LB#= VIL
3. Address must be valid prior to or coincident with CE# and (UB# and, or LB#) transition now.
4. OE# = VIL.
5. tCLZ , tOLZ, tCHZ, and tOHZ are specified with CL=5pF. Transition is measured \pm 500mV from steady state.
6. At any given temperature and voltage condition, tCHZ is less than tCLZ , tOHZ is less than tOLZ.



WRITE CYCLE 1 (WE# Controlled) (1,2,3,5)



WRITE CYCLE 2 (CE#) (1,2,5)





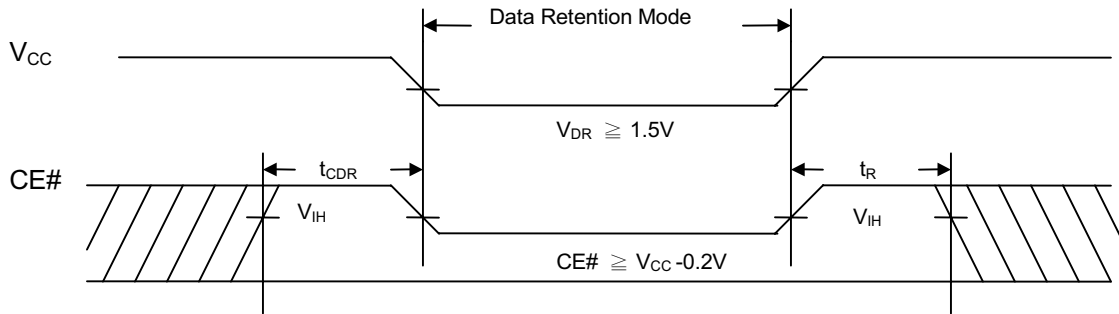
Notes :

1. WE# or CE# must be HIGH during all address transitions.
2. A write occurs during the overlap of a low CE# and a low WE#.
3. During a WE# controlled with write cycle with OE# LOW, t_{WP} must be greater than $t_{WHZ}+t_{DW}$ to allow the I/O drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the CE# LOW transition occurs simultaneously with or after WE# LOW transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L=5pF$. Transition is measured $\pm 500mV$ from steady state.

DATA RETENTION CHARACTERISTICS (TA = 0°C to 70°C / -40°C to 85°C (I))

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	VDR	CE1# \geq VCC-0.2V or CE2 \leq 0.2V	1.5	-	-	V
Data Retention Current	IDR	Vcc=1.5V CE1# \geq VCC-0.2V or CE2 \leq 0.2V	-	-	10	μ A
Chip Disable to Data Retention Time	tCDR	See Data Retention Waveforms(below)	0	-	-	ms
Recovery Time	tR		5	-	-	ms

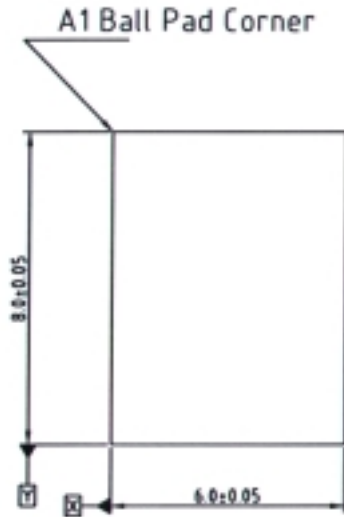
DATA RETENTION WAVEFORM



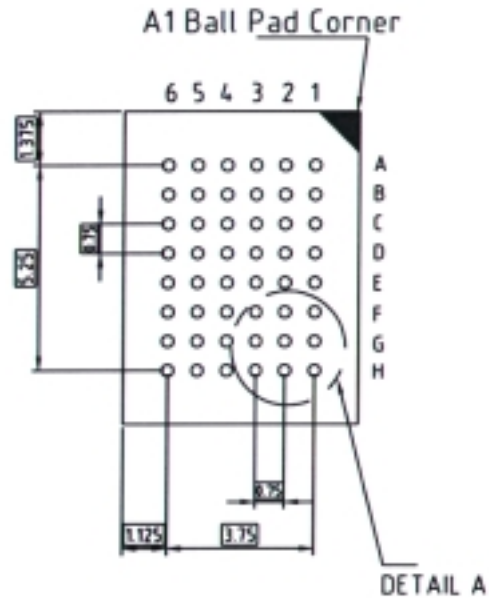


PACKAGE OUTLINE DIMENSION

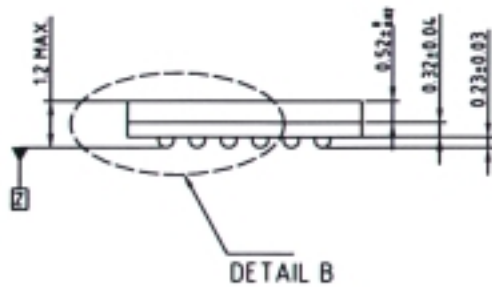
48 BALL 6.0X8.0mm , 0.75mm BALL PITCH, TFBGA PACKAGE OUTLINE DIMENSION



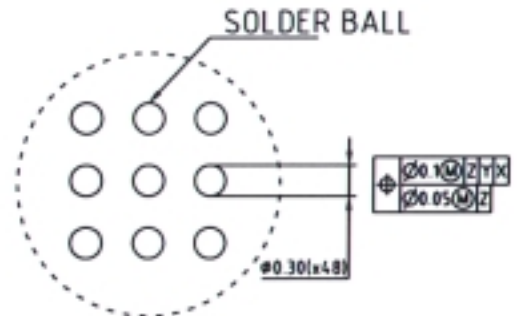
TOP VIEW (DIE VIEW)



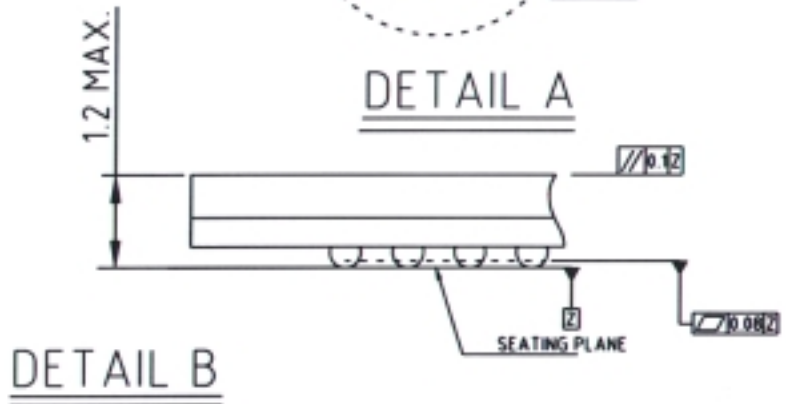
BOTTOM VIEW (BALL SIDE)



SIDE VIEW



DETAIL A



DETAIL B



UTRON

Preliminary Rev. 0.5

UT62L12916(I)
128K X 16 BIT LOW-POWER CMOS SRAM

ORDERING INFORMATION

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μA) max	PACKAGE
UT62L12916BS-70L	70	80	48PIN BGA
UT62L12916BS-70LL	70	25	48PIN BGA
UT62L12916BS-100L	100	80	48PIN BGA
UT62L12916BS-100LL	100	25	48PIN BGA